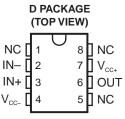


TLV7211, TLV7211A CMOS COMPARATORS WITH RAIL-TO-RAIL INPUT AND PUSH-PULL OUTPUT SLCS149B-AUGUST 2006-REVISED JANUARY 2007

FEATURES

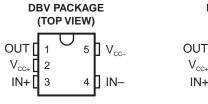
- Parameters Specified at 2.7-V, 5-V, and 15-V Supplies
- Supply Current 7 μA (Typ) at 5 V
- Response Time 4 μ s (Typ) at 5 V
- Push-Pull Output
- Input Common-Mode Range Beyond
 V_{CC-} and V_{CC+}
- Low Input Current

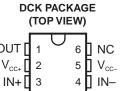


NC – No internal connection

APPLICATIONS

- Battery-Powered Products
- Notebooks and PDAs
- Mobile Communications
- Alarm and Security Circuits
- Direct Sensor Interface
- Replaces Amplifiers Used as Comparators With Better Performance and Lower Current





DESCRIPTION/ORDERING INFORMATION

The TLV7211 and TLV7211A are micropower CMOS comparators available in the space-saving SOT-23-5 package. This makes the comparators ideal for space- and weight-critical designs. The TLV7211A features an input offset voltage of 5 mV, and the TLV7211 features an input offset voltage of 15 mV.

The main benefits of the SOT-23-5 package are most apparent in small portable electronic devices, such as mobile phones, pagers, notebook computers, personal digital assistants, and PCMCIA cards. The rail-to-rail input voltage makes the TLV7211 or TLV7211A a good choice for sensor interfacing, such as light detector circuits, optical and magnetic sensors, and alarm and status circuits.

The SOT-23-5 package's small size allows it to fit into tight spaces on PC boards.

ORDERING INFORMATION

T _A	V _{OS} (MAX)	PACKAGE ⁽¹⁾		ORDERABLE PART NUMBER	TOP-SIDE MARKING ⁽²⁾
		SOIC – D	Reel of 2500	TLV7211AIDR	7211AI
		50IC - D	Tube of 75	TLV7211AID	7211AI
	5 mV	SOT-23-5 – DBV	Reel of 3000	TLV7211AIDBVR	YBN_
			Reel of 3000	TLV7211AIDCKR	Vo
–40°C to 85°C		SOT (SC-70) – DCK	Reel of 250	TLV7211AIDCKT	- Y8_
-40°C 10 85°C		SOIC – D	Reel of 2500	TLV7211IDR	TY7211
		50IC - D	Tube of 75	TLV7211ID	117211
	15 mV	SOT-23-5 – DBV	Reel of 3000	TLV7211IDBVR	YBK_
			Reel of 3000	TLV7211IDCKR	V7
		SOT (SC-70) – DCK	Reel of 250	TLV7211IDCKT	Y7_

(1) Package drawings, standard packing quantities, thermal data, symbolization, and PCB design guidelines are available at www.ti.com/sc/package.

(2) DBV/DCK: The actual top-side marking has one additional character that designates the assembly/test site.

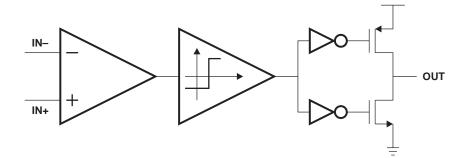


Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet.

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TEXAS INSTRUMENTS www.ti.com

FUNCTIONAL BLOCK DIAGRAM



Absolute Maximum Ratings⁽¹⁾

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
$V_{CC+} - V_{CC-}$	Supply voltage ⁽²⁾			16	V
V _{ID}	Differential input voltage ⁽³⁾			±Supply voltage	V
VI	Input voltage range (any input)		$V_{CC-} - 0.3$	$V_{CC+} + 0.3$	V
Vo	Output voltage range		$V_{CC-} - 0.3$	V _{CC+} + 0.3	V
I _{CC}	Supply current			40	mA
I _I	Input current			±5	mA
I _O	Output current			±30	mA
		D package		97	
θ_{JA}	Package thermal impedance ⁽⁴⁾⁽⁵⁾	DBV package		206	°C/W
		DCK package		259	
TJ	Operating virtual junction temperature	· · · ·		150	°C
T _{stg}	Storage temperature range		-65	150	°C

(1) Stresses beyond those listed under "absolute maximum ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under "recommended operating conditions" is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

(2) All voltage values (except differential voltages and V_{CC} specified for the measurement of I_{OS}) are with respect to the network GND.

(3) Differential voltages are at IN+ with respect to IN-.

(4) Maximum power dissipation is a function of T_J(max), θ_{JA}, and T_A. The maximum allowable power dissipation at any allowable ambient temperature is P_D = (T_J(max) – T_A)/θ_{JA}. Operating at the absolute maximum T_J of 150°C can affect reliability.

(5) The package thermal impedance is calculated in accordance with JESD 51-7.

ESD Protection

	TYP	UNIT
Human-Body Model	2000	V

Recommended Operating Conditions

		MIN	MAX	UNIT
$V_{CC+} - V_{CC-}$	Supply voltage	2.7	15	V
TJ	Operating virtual junction temperature	-40	85	°C

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2.7-V Electrical Characteristics

 V_{CC+} = 2.7 V, V_{CC-} = GND, V_{CM} = V_{O} = $V_{CC+}/2$, and R_L > 1 M Ω (unless otherwise noted)

		TEST CONDITIONS		TL	V7211A	\	т	LV7211		
	PARAMETER	TEST CONDITIONS	T _J	MIN	TYP	MAX	MIN	TYP	MAX	UNIT
V	Input offect veltere		25°C		3	5		3	15	mV
V _{OS}	Input offset voltage		–40°C to 85°C			8			18	mv
TCV _{OS}	Input offset voltage temperature drift		25°C		1			1		μV/°C
	Input offset voltage average drift ⁽¹⁾		25°C		3.3			3.3		μV/month
I _B	Input current		25°C		0.04			0.04		pА
I _{OS}	Input offset current		25°C		0.02			0.02		pА
CMRR	Common-mode rejection ratio	$0 \le V_{CM} \le 2.7 \text{ V}$	25°C		75			75		dB
PSRR	Power-supply rejection ratio	$2.7 \text{ V} \leq \text{V}_{\text{CC+}} \leq 15 \text{ V}$	25°C		80			80		dB
A _V	Voltage gain		25°C		100			100		dB
			25°C	2.9	3		2.9	3		
CMVR	Input common-mode	CMRR > 55 dB	–40°C to 85°C	2.7			2.7			V
CIVIVR	voltage range	CMRR > 55 dB	25°C		-0.3	-0.2		-0.3	-0.2	v
		CIVIER > 55 UD	–40°C to 85°C			0			0	
V	High-level output	L _ 2.5 m/	25°C	2.4	2.5		2.4	2.5		V
V _{OH}	voltage	$I_{load} = 2.5 \text{ mA}$	–40°C to 85°C	2.3			2.3			v
V	Low-level output	L _ 2.5 m/	25°C		0.2	0.3		0.2	0.3	V
V _{OL}	voltage	$I_{load} = 2.5 \text{ mA}$	–40°C to 85°C			0.4			0.4	v
			25°C		7	12		7	12	
	Cupply ourrept	V _{OUT} = Low	–40°C to 85°C			14			14	
I _{CC}	Supply current		25°C		5	10		5	10	μA
		V _{OUT} = High-Idle	-40°C to 85°C			12			12	

(1) Input offset voltage average drift is calculated by dividing the accelerated operating life V_{OS} drift by the equivalent operational time. This represents worst-case input conditions and includes the first 30 days of drift.

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5-V Electrical Characteristics

 V_{CC+} = 5 V, V_{CC-} = GND, V_{CM} = V_{O} = $V_{CC+}/2,$ and R_L > 1 $M\Omega$ (unless otherwise noted)

		TEST CONDITIONS	–	TL	V7211	4	т	LV7211		
	PARAMETER	TEST CONDITIONS	Tj	MIN	TYP	MAX	MIN	TYP	MAX	UNIT
V	Innut offert veltage		25°C		3	5		3	15	m)/
V _{OS}	Input offset voltage		–40°C to 85°C			8			18	mV
TCV _{OS}	Input offset voltage temperature drift		25°C		1			1		μV/°C
	Input offset voltage average drift ⁽¹⁾		25°C		3.3			3.3		μV/month
I _B	Input current		25°C		0.04			0.04		pА
I _{OS}	Input offset current		25°C		0.02			0.02		pА
CMRR	Common-mode rejection ratio		25°C		75			75		dB
PSRR	Power-supply rejection ratio	$5 \text{ V} \leq \text{V}_{\text{CC+}} \leq 10 \text{ V}$	25°C		80			80		dB
A _V	Voltage gain		25°C		100			100		dB
		CMRR > 55 dB	25°C	5.2	5.3		5.2	5.3		
CMVR	Input common-mode	CIVIRR > 55 UD	–40°C to 85°C	5			5			V
CIVIVR	voltage range	CMRR > 55 dB	25°C		-0.3	-0.2		-0.3	-0.2	v
		CIVIER > 55 UD	–40°C to 85°C			0			0	
V	High-level output	L - 5 m A	25°C	4.6	4.8		4.6	4.8		V
V _{OH}	voltage	$I_{load} = 5 \text{ mA}$	$-40^{\circ}C$ to $85^{\circ}C$	4.45			4.45			v
V	Low-level output	L - 5 m A	25°C		0.2	0.4		0.2	0.4	V
V _{OL}	voltage	I _{load} = 5 mA	$-40^{\circ}C$ to $85^{\circ}C$			0.55			0.55	v
			25°C		7	14		7	14	
	Supply current	V _{OUT} = Low	$-40^{\circ}C$ to $85^{\circ}C$			18			18	μA
I _{CC}		V _{OUT} = High-Idle	25°C		5	10		5	10	μΑ
			–40°C to 85°C			13			13	
I _{OH}	Short-circuit output current	Isource	25°C	30			30			mA
I _{OL}	Short-circuit output current	I_{sink} , $V_O < 12 V^{(2)}$	25°C	45			45			mA

(1) Input offset voltage average drift is calculated by dividing the accelerated operating life V_{OS} drift by the equivalent operational time. This represents worst-case input conditions and includes the first 30 days of drift.

(2) Do not short circuit the output to V+ if V+ is >12 V.



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15-V Electrical Characteristics

 V_{CC+} = 15 V, V_{CC-} = GND, V_{CM} = V_{O} = $V_{CC+}/2$, and R_{L} > 1 M Ω (unless otherwise noted)

		TEST	-	тι	_V7211A	\	т	LV7211		
	PARAMETER	CONDITIONS	Τ _J	MIN	TYP	MAX	MIN	TYP	MAX	UNIT
\ <i>\</i>	lanut effect veltere		25°C		3	5		3	15	
V _{OS}	Input offset voltage		–40°C to 85°C			8			18	mV
TCV _{OS}	Input offset voltage temperature drift		25°C		4			4		μV/°C
	Input offset voltage average drift ⁽¹⁾		25°C		4			4		μV/month
I _B	Input current		25°C		0.04			0.04		pА
l _{os}	Input offset current		25°C		0.02			0.02		pА
CMRR	Common-mode rejection ratio		25°C		82			82		dB
PSRR	Power-supply rejection ratio	$5 \text{ V} \leq \text{V}_{\text{CC+}} \leq 10 \text{ V}$	25°C		80			80		dB
A _V	Voltage gain		25°C		100			100		dB
		CMRR > 55 dB	25°C	15.2	15.3		15.2	15.3		
CMVR	Input common-mode voltage	CIVIER > 55 GB	$-40^{\circ}C$ to $85^{\circ}C$	15			15			V
CIVIVIN	range	CMRR > 55 dB	25°C		-0.3	-0.2		-0.3	-0.2	v
		CIVIER > 55 GB	$-40^{\circ}C$ to $85^{\circ}C$			0			0	
V	High-level output voltage	$l_{1} = 5 \text{ mA}$	25°C	14.6	14.8		14.6	14.8		V
V _{OH}	riigh-level output voltage	$I_{load} = 5 \text{ mA}$	$-40^{\circ}C$ to $85^{\circ}C$	14.45			14.45			v
V	Low-level output voltage	I _{load} = 5 mA	25°C		0.2	0.4		0.2	0.4	V
V _{OL}	Low-level output voltage	Iload = 5 IIIA	$-40^{\circ}C$ to $85^{\circ}C$			0.55			0.55	v
		V _{OUT} = Low	25°C		7	14		7	14	
1	Supply current	VOUT = LOW	-40° C to 85° C			18			18	μA
I _{CC}	Supply current	V _{OUT} = High-Idle	25°C		5	12		5	12	μΑ
			–40°C to 85°C			14			14	
I _{OH}	Short-circuit output current	I _{source}	25°C	30			30			mA
I _{OL}	Short-circuit output current	I_{sink} , $V_O < 12 V^{(2)}$	25°C	45			45			mA

(1) Input offset voltage average drift is calculated by dividing the accelerated operating life V_{OS} drift by the equivalent operational time. This represents worst-case input conditions and includes the first 30 days of drift.

(2) Do not short circuit the output to V+ if V+ is >12 V.

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Switching Characteristics

 $T_{\rm J}=25^{\circ}C,~V_{\rm CC+}=5~V,~V_{\rm CC-}=GND,~V_{\rm CM}=V_{\rm O}=V_{\rm CC+}/2,~\text{and}~R_{\rm L}>1~M\Omega~(\text{unless otherwise noted})$

	PARAMETER	TEST CONDITIONS		TYP	UNIT
t _{rise}	Rise time	$f = 10 \text{ kHz}, C_L = 50 \text{ pF}^{(1)}, \text{ Overdrive} = 10 \text{ mV}$,	0.3	μs
t _{fall}	Fall time	$f = 10 \text{ kHz}, C_L = 50 \text{ pF}^{(1)}, \text{ Overdrive} = 10 \text{ mV}$		0.3	μs
		f_{1} 10 kHz C = 50 p $\Gamma^{(1)}$	10 mV	10	
	Drangestion delay time, high to $low^{(2)}$	$f = 10 \text{ kHz}, C_L = 50 \text{ pF}^{(1)}$	100 mV	4	
t _{PHL}	Propagation delay time, high to $low^{(2)}$	(1)	10 mV	10	μs
		$V_{CC+} = 2.7 \text{ V}, \text{ f} = 10 \text{ kHz}, \text{ C}_{L} = 50 \text{ pF}^{(1)}$	100 mV	4	
			10 mV	6	
	Description delegations have to bist (2)	$f = 10 \text{ kHz}, C_{L} = 50 \text{ pF}^{(1)}$	100 mV	4	_
t _{PLH}	Propagation delay time, low to high ⁽²⁾		10 mV	7	μs
		$V_{CC+} = 2.7 \text{ V}, \text{ f} = 10 \text{ kHz}, C_{L} = 50 \text{ pF}^{(1)}$	100 mV	4	

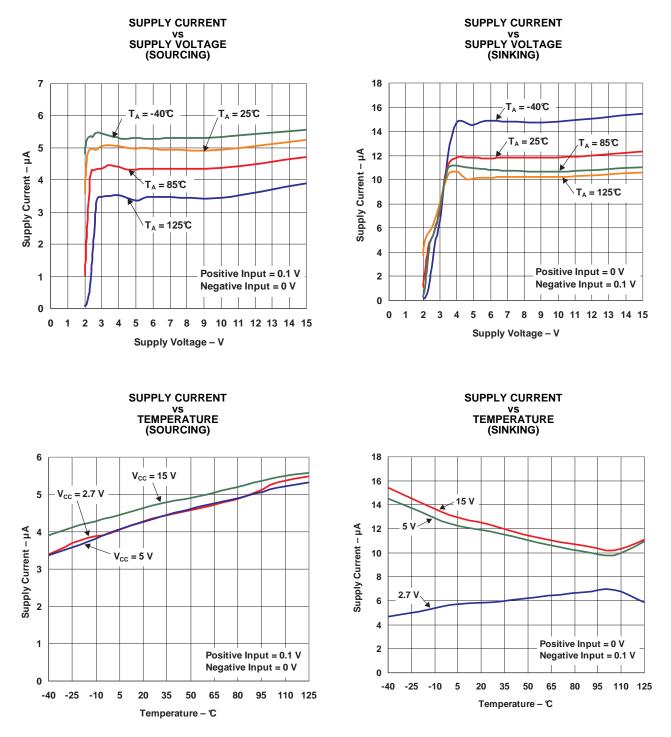
C_L includes probe and jig capacitance.
 Input step voltage for propagation delay measurement is 2 V.





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TYPICAL CHARACTERISTICS

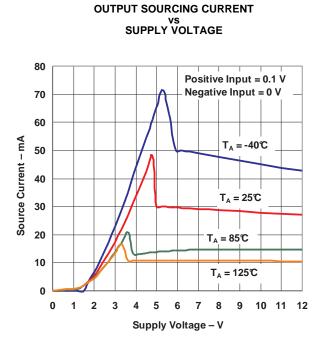




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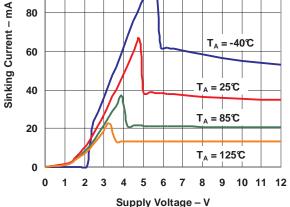


TYPICAL CHARACTERISTICS (continued)

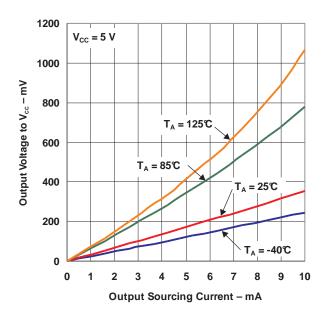


vs SUPPLY VOLTAGE 120 Positive Input = 0.1 V Negative Input = 0 V 100 80 T_A = -40℃ 60

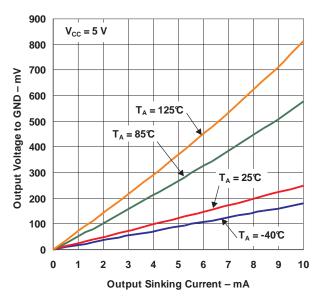
OUTPUT SINKING CURRENT



OUTPUT VOLTAGE VS OUTPUT SOURCING CURRENT



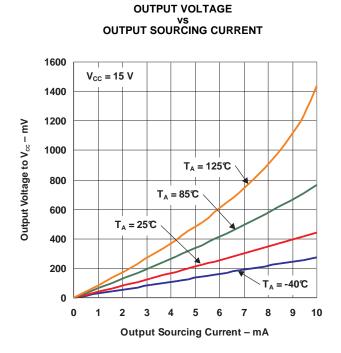


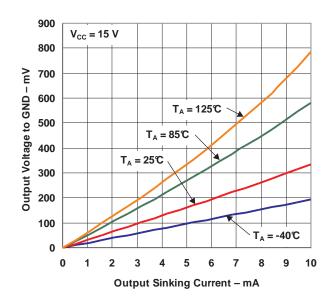




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TYPICAL CHARACTERISTICS (continued)





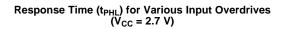
OUTPUT VOLTAGE

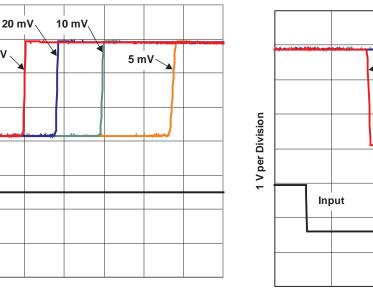
VS OUTPUT SINKING CURRENT

Response Time (t_{PLH}) for Various Input Overdrives (V_{CC} = 2.7 V)

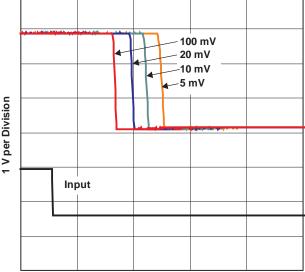
100 mV

1 V per Division





2 μs per Division



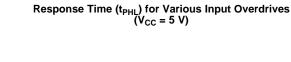
2 µs per Division

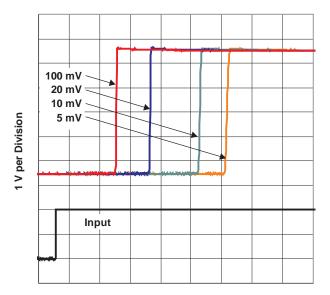
TLV7211, TLV7211A CMOS COMPARATORS WITH RAIL-TO-RAIL INPUT AND PUSH-PULL OUTPUT SLCS149B-AUGUST 2006-REVISED JANUARY 2007



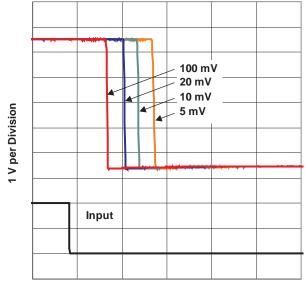
TYPICAL CHARACTERISTICS (continued)

Response Time (t_{PLH}) for Various Input Overdrives ($V_{CC} = 5 V$)

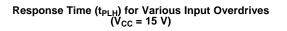


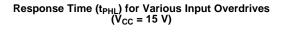


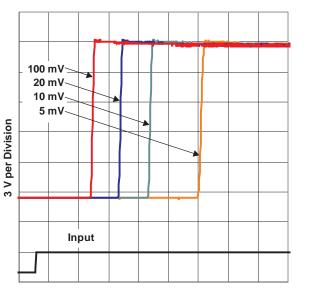
2 µs per Division



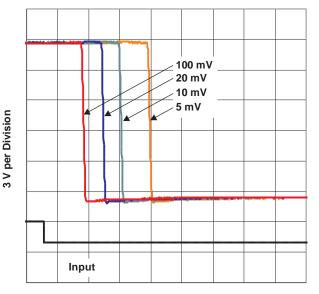
2 µs per Division







 $2\,\mu s$ per Division



2 µs per Division

Submit Documentation Feedback



PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
							(6)				
TLV7211AID	ACTIVE	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	7211AI	Samples
TLV7211AIDBVR	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 85	YBNM	Samples
TLV7211AIDCKR	ACTIVE	SC70	DCK	6	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 85	Y8A	Samples
TLV7211AIDCKT	OBSOLETE	SC70	DCK	6		TBD	Call TI	Call TI	-40 to 85	Y8A	
TLV7211AIDR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	7211AI	Samples
TLV7211ID	ACTIVE	SOIC	D	8	75	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	TY7211	Samples
TLV7211IDBVR	ACTIVE	SOT-23	DBV	5	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 85	YBKM	Samples
TLV7211IDCKR	ACTIVE	SC70	DCK	6	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 85	Y7A	Samples
TLV7211IDCKT	OBSOLETE	SC70	DCK	6		TBD	Call TI	Call TI	-40 to 85	Y7A	
TLV7211IDR	ACTIVE	SOIC	D	8	2500	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 85	TY7211	Samples

⁽¹⁾ The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

⁽²⁾ RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

⁽³⁾ MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

⁽⁴⁾ There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.



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PACKAGE OPTION ADDENDUM

⁽⁵⁾ Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

⁽⁶⁾ Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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Texas

STRUMENTS

TAPE AND REEL INFORMATION





QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal												
Device	Package Type	Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
TLV7211AIDBVR	SOT-23	DBV	5	3000	178.0	9.0	3.3	3.2	1.4	4.0	8.0	Q3
TLV7211AIDCKR	SC70	DCK	6	3000	180.0	8.4	2.41	2.41	1.2	4.0	8.0	Q3
TLV7211AIDCKT	SC70	DCK	6	250	180.0	8.4	2.41	2.41	1.2	4.0	8.0	Q3
TLV7211AIDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1
TLV7211IDBVR	SOT-23	DBV	5	3000	178.0	9.0	3.23	3.17	1.37	4.0	8.0	Q3
TLV7211IDCKR	SC70	DCK	6	3000	180.0	8.4	2.41	2.41	1.2	4.0	8.0	Q3
TLV7211IDR	SOIC	D	8	2500	330.0	12.4	6.4	5.2	2.1	8.0	12.0	Q1



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PACKAGE MATERIALS INFORMATION

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Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
TLV7211AIDBVR	SOT-23	DBV	5	3000	180.0	180.0	18.0
TLV7211AIDCKR	SC70	DCK	6	3000	202.0	201.0	28.0
TLV7211AIDCKT	SC70	DCK	6	250	202.0	201.0	28.0
TLV7211AIDR	SOIC	D	8	2500	340.5	338.1	20.6
TLV7211IDBVR	SOT-23	DBV	5	3000	180.0	180.0	18.0
TLV7211IDCKR	SC70	DCK	6	3000	202.0	201.0	28.0
TLV7211IDR	SOIC	D	8	2500	340.5	338.1	20.6

TEXAS INSTRUMENTS

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TUBE



- B - Alignment groove width

*All dimensions are nominal

Device	Package Name	Package Type	Pins	SPQ	L (mm)	W (mm)	Τ (μm)	B (mm)
TLV7211AID	D	SOIC	8	75	507	8	3940	4.32
TLV7211ID	D	SOIC	8	75	507	8	3940	4.32

D0008A



PACKAGE OUTLINE

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES:

1. Linear dimensions are in inches [millimeters]. Dimensions in parenthesis are for reference only. Controlling dimensions are in inches. Dimensioning and tolerancing per ASME Y14.5M.

- 2. This drawing is subject to change without notice.
- 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed .006 [0.15] per side.
- 4. This dimension does not include interlead flash.
- 5. Reference JEDEC registration MS-012, variation AA.



D0008A

EXAMPLE BOARD LAYOUT

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



D0008A

EXAMPLE STENCIL DESIGN

SOIC - 1.75 mm max height

SMALL OUTLINE INTEGRATED CIRCUIT



NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

9. Board assembly site may have different recommendations for stencil design.



DBV0005A



PACKAGE OUTLINE

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 This drawing is subject to change without notice.
 Reference JEDEC MO-178.

- 4. Body dimensions do not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not exceed 0.25 mm per side.
- 5. Support pin may differ or may not be present.



DBV0005A

EXAMPLE BOARD LAYOUT

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.

7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



DBV0005A

EXAMPLE STENCIL DESIGN

SOT-23 - 1.45 mm max height

SMALL OUTLINE TRANSISTOR



NOTES: (continued)

8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

9. Board assembly site may have different recommendations for stencil design.



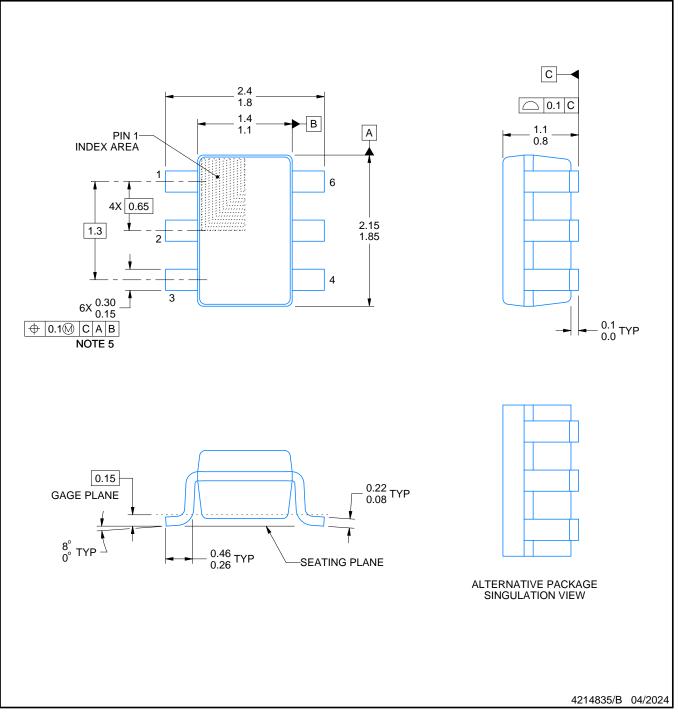
DCK0006A



PACKAGE OUTLINE

SOT - 1.1 max height

SMALL OUTLINE TRANSISTOR



NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
 This drawing is subject to change without notice.
 Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
 Falls within JEDEC MO-203 variation AB.

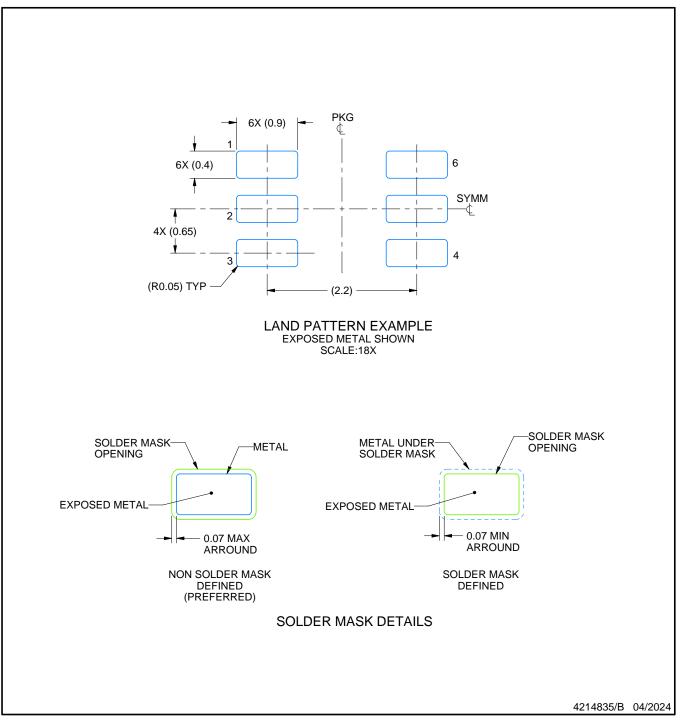


DCK0006A

EXAMPLE BOARD LAYOUT

SOT - 1.1 max height

SMALL OUTLINE TRANSISTOR



NOTES: (continued)

5. Publication IPC-7351 may have alternate designs.

6. Solder mask tolerances between and around signal pads can vary based on board fabrication site.

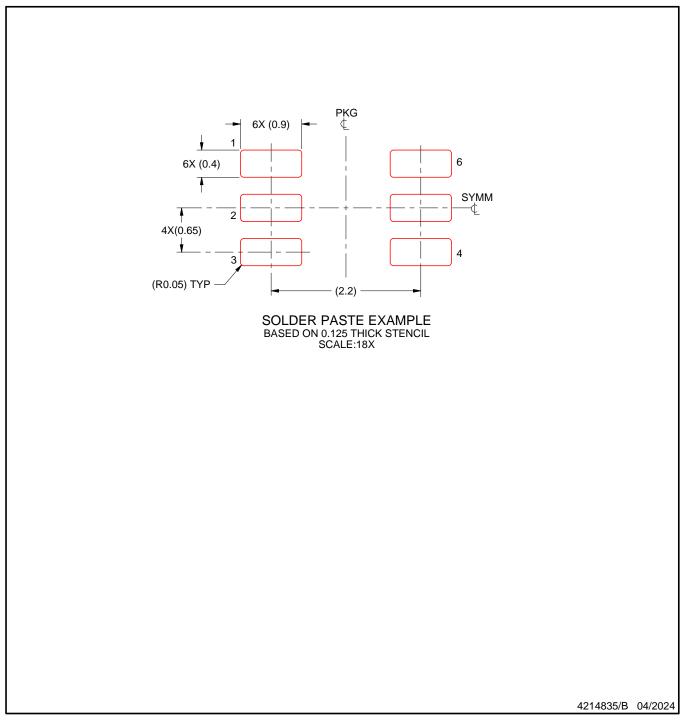


DCK0006A

EXAMPLE STENCIL DESIGN

SOT - 1.1 max height

SMALL OUTLINE TRANSISTOR



NOTES: (continued)

8. Board assembly site may have different recommendations for stencil design.



^{7.} Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

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